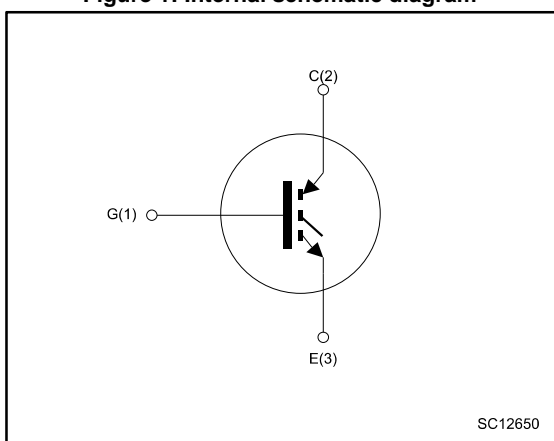


Figure 1: Internal schematic diagram



### Features

- High frequency operation
- Low  $C_{RES}$  /  $C_{IES}$  ratio (no cross-conduction susceptibility)

### Applications

- High frequency inverters
- High frequency motor controls, inverters, UPS
- HF, SMPS and PFC in both hard switch and resonant topologies

### Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

Table 1: Device summary

Order code	Marking	Package	Packaging
STGW19NC60W	GW19NC60W	TO-247	Tube

**Contents**

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# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0)	600	V
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 25 °C	42	A
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 100 °C	23	A
I <sub>CL</sub> <sup>(2)</sup>	Turn-off latching current	30	A
V <sub>GE</sub>	Gate-emitter voltage	±20	V
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	140	W
T <sub>stg</sub>	Storage temperature range	- 55 to 150	°C
T <sub>J</sub>	Operating junction temperature range		

**Notes:**

<sup>(1)</sup>Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_{J(max)} \times I_C(T_C))}$$

<sup>(2)</sup>V<sub>CLAMP</sub> = 80% (V<sub>CES</sub>), V<sub>GE</sub> = 15 V, R<sub>G</sub> = 10 Ω, T<sub>J</sub> = 150 °C

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.9	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	50	°C/W

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 4: Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$ , $I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$ , $I_C = 12\text{ A}$		2.1	2.5	V
		$V_{GE} = 15\text{ V}$ , $I_C = 12\text{ A}$ , $T_J = 125\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$			150	$\mu\text{A}$
		$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_C = 125\text{ °C}$ <sup>(1)</sup>			1	mA
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100$	nA
$g_{fs}$	Forward transconductance	$V_{CE} = 15\text{ V}$ , $I_C = 12\text{ A}$		10		S

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0\text{ V}$	-	1180	-	pF
$C_{oes}$	Output capacitance		-	130	-	
$C_{res}$	Reverse transfer capacitance		-	26	-	
$Q_g$	Total gate charge	$V_{CE} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ (see <a href="#">Figure 16: "Gate charge test circuit"</a> )	-	53	-	nC
$Q_{ge}$	Gate-emitter charge		-	10	-	
$Q_{gc}$	Gate-collector charge		-	21	-	

Table 6: Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	25	-	ns
$t_r$	Current rise time		-	7	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1600	-	A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ , $T_C = 125^\circ\text{C}$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	25	-	ns
$t_r$	Current rise time		-	8	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1400	-	A/ $\mu$ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	22	-	ns
$t_{d(off)}$	Turn-off delay time		-	90	-	ns
$t_f$	Current fall time		-	43	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ , $T_C = 125^\circ\text{C}$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	47	-	ns
$t_{d(off)}$	Turn-off delay time		-	127	-	ns
$t_f$	Current fall time		-	77	-	ns

Table 7: Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	81	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	125	-	$\mu$ J
$E_{ts}$	Total switching energy		-	206	-	$\mu$ J
$E_{on}^{(1)}$	Turn-on switching energy		-	161	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	255	-	$\mu$ J
$E_{ts}$	Total switching energy	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_C = 125^\circ\text{C}$ (see <a href="#">Figure 17: "Switching waveform"</a> )	-	416	-	$\mu$ J

**Notes:**

<sup>(1)</sup>Including the reverse recovery of the external diode. The diode is the same of the co-packed STGW19NC60WD.

<sup>(2)</sup>Including the tail of the collector current.

## 2.2 Electrical characteristics (curves)

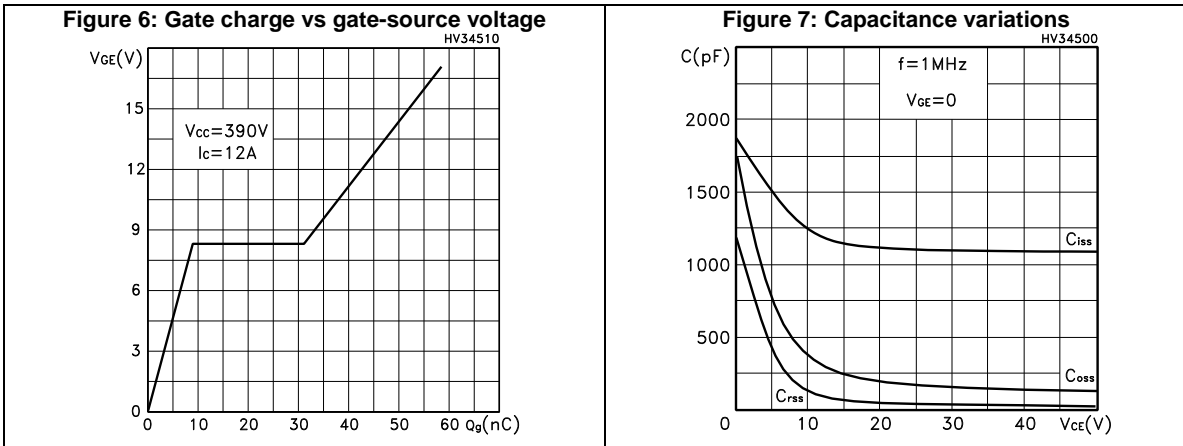
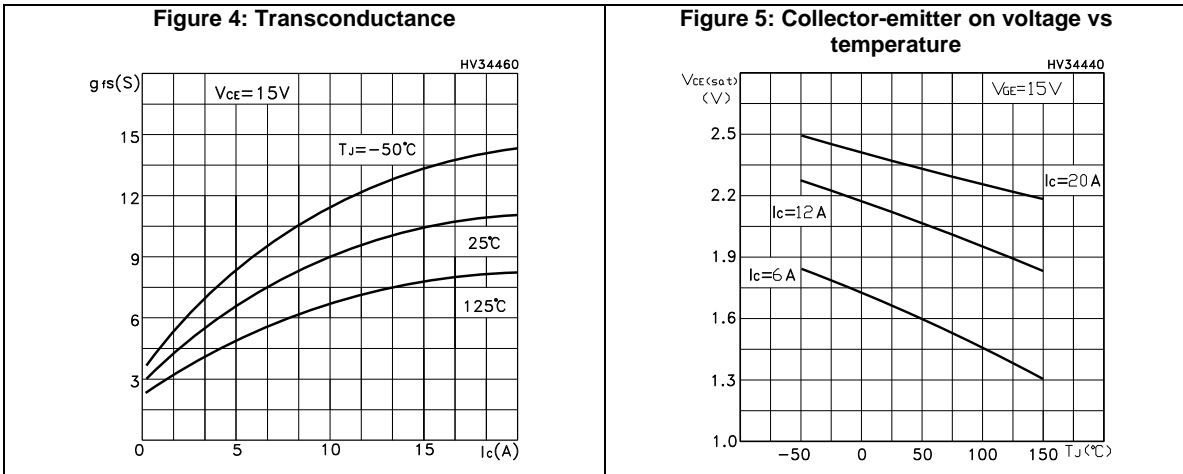
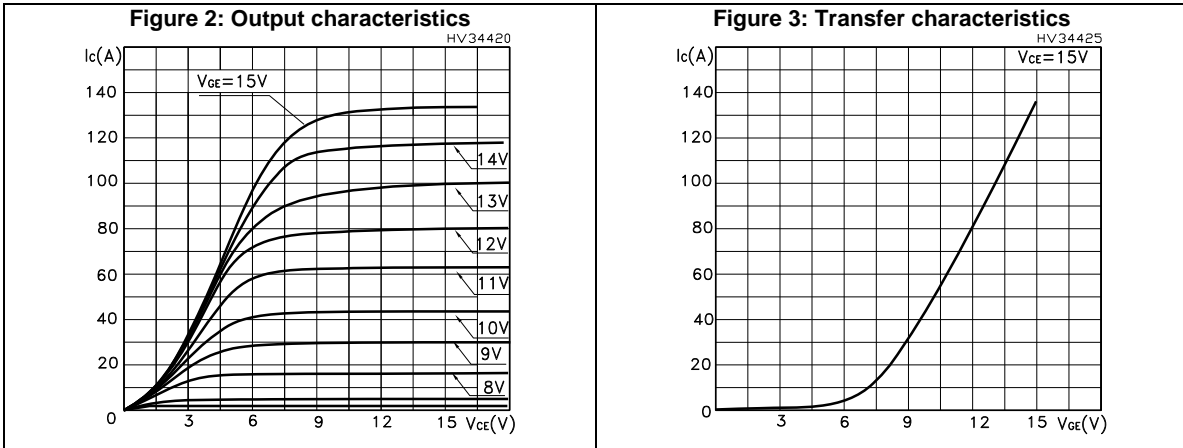


Figure 8: Normalized gate threshold voltage vs temperature

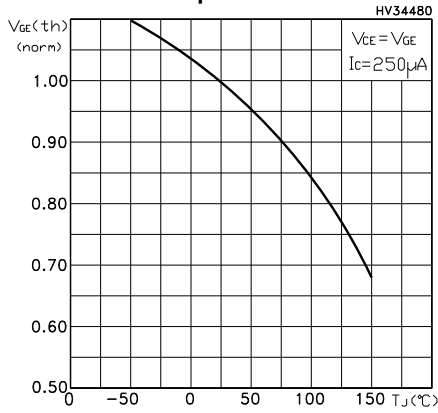


Figure 9: Collector-emitter on voltage vs collector current

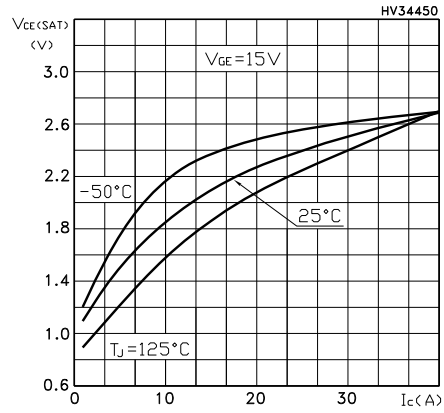


Figure 10: Normalized breakdown voltage vs temperature

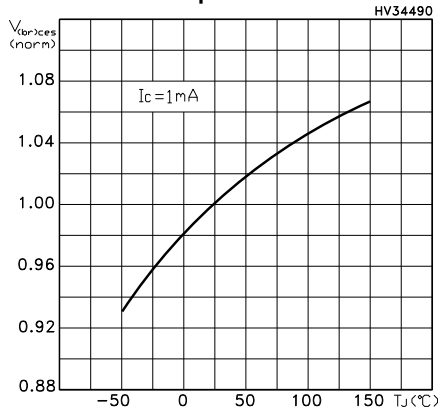


Figure 11: Switching energy vs temperature

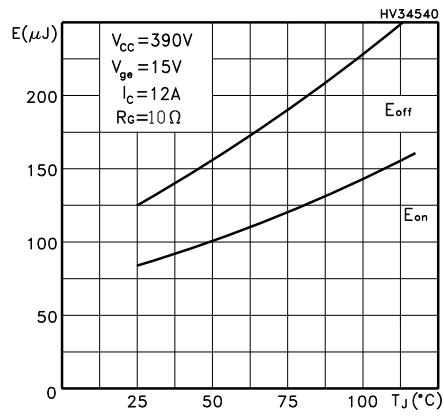


Figure 12: Switching energy vs gate resistance

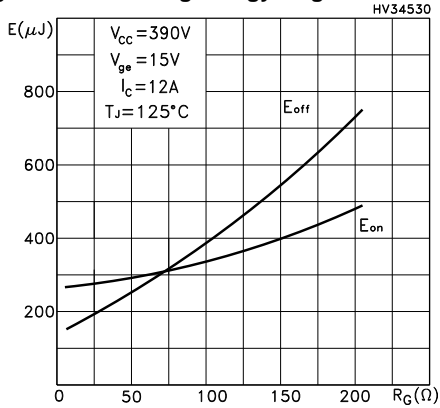


Figure 13: Switching energy vs collector current

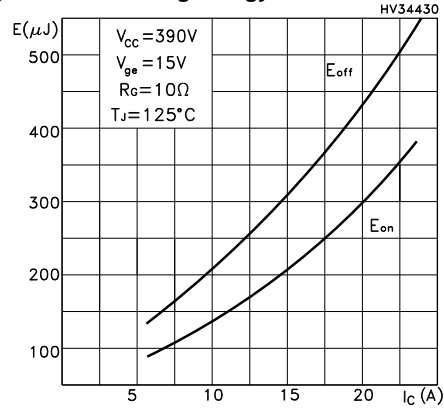
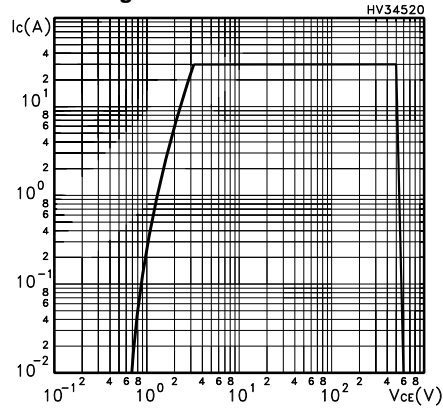
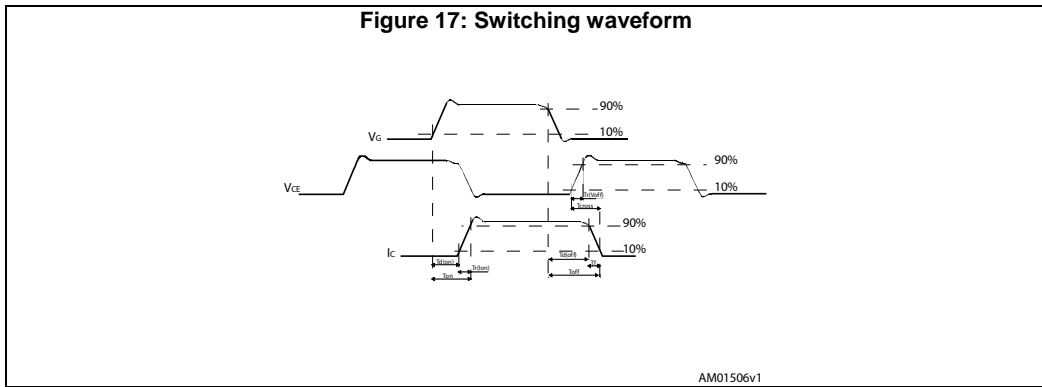
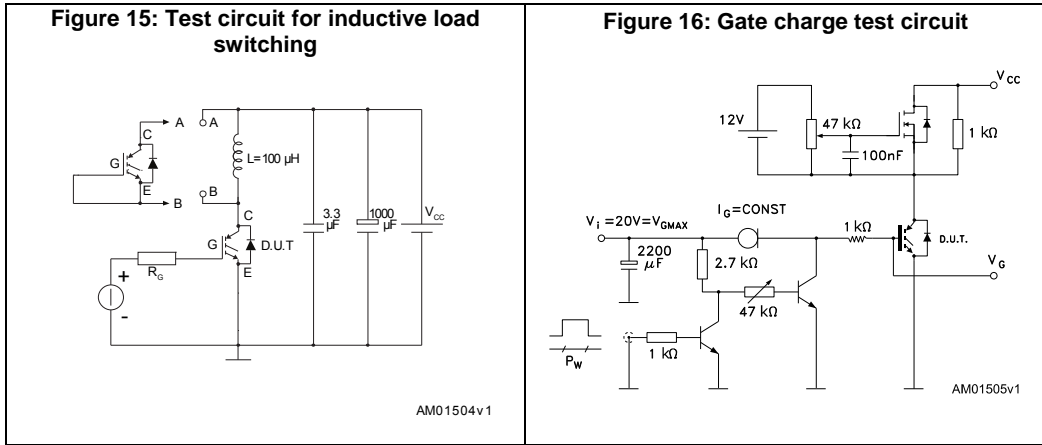


Figure 14: Turn-off SOA





### 3 Test circuits



## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-247 package information

Figure 18: TO-247 package outline

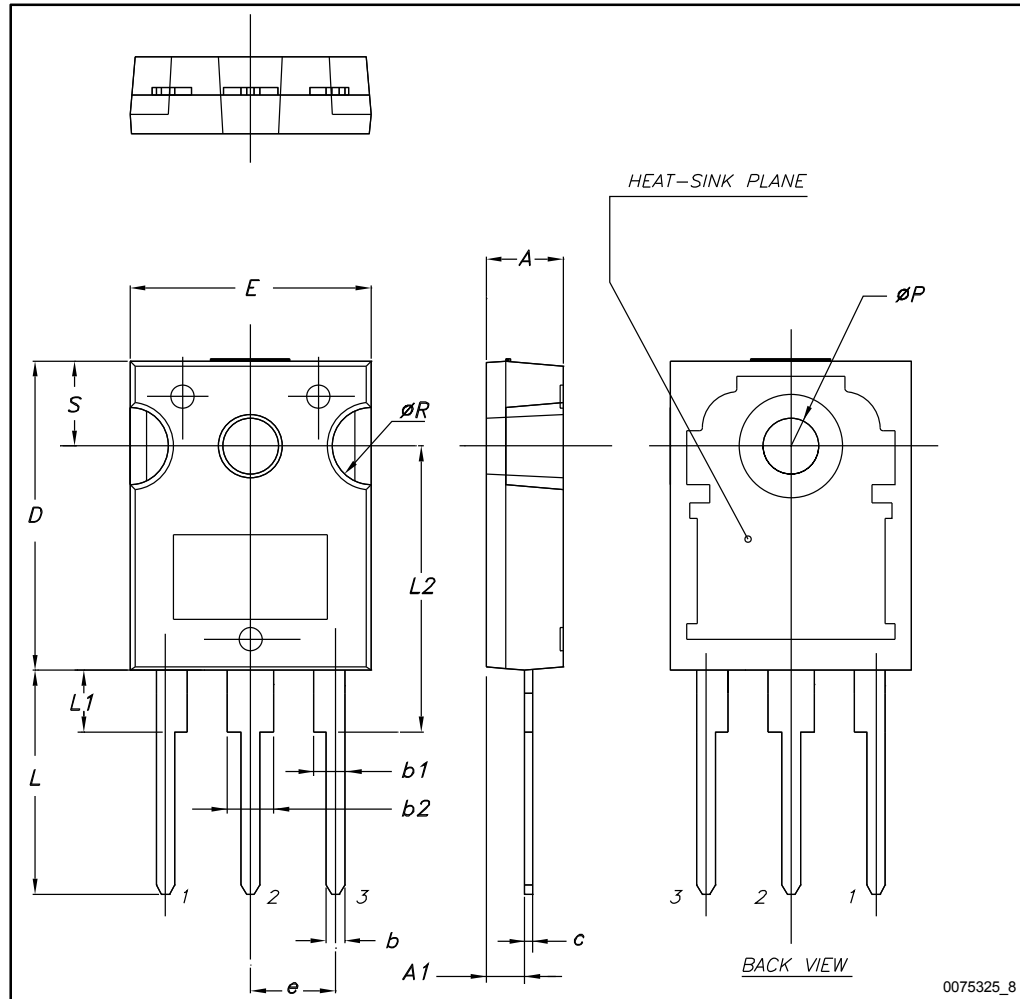


Table 8: TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
04-Oct-2006	1	Initial release.
08-May-2007	2	Modified value on <i>Table 2</i>
20-Nov-2008	3	Inserted packages: D2PAK and TO-247
07-Nov-2016	4	The part numbers STGB19NC60W and STGP19NC60W have been moved to a separate datasheet Modified: <a href="#">Table 2: "Absolute maximum ratings"</a> , <a href="#">Table 4: "Static"</a> and <a href="#">Table 7: "Switching energy (inductive load)"</a> Minor text changes

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